

Abstract

A semiconductor component and a method of manufacturing it are described, making it possible to provide a switching element for high switching frequencies without the omnipresent leakage inductance resulting in high interference voltage peaks. Therefore, pits are produced in the surface of the wafer, resulting in a middle zone (10) having a variable thickness laterally. First areas (40) of this middle zone (10) guarantee a gentle drop in clearing current, second areas (50) guarantee short switching times and a low forward voltage.

(Figure 3a)